



Calculation of the valence band offsets of common anion semiconductor heterojunctions from core levels: The role of cation d orbitals

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CONDUCTION AND VALENCE BAND OFFSETS IN A Heterostructure of GaAs and AlGaAs





TABLE II. True chemical shifts (TCS), in eV, of the anion 1s level in different semiconductor pairs, using various cation core levels as reference. The common core level of the compound to the right hand side of each pair is

The table content is illegible due to extreme image noise and corruption. The structure of the table is not discernible.





